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(54) Title: A METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE

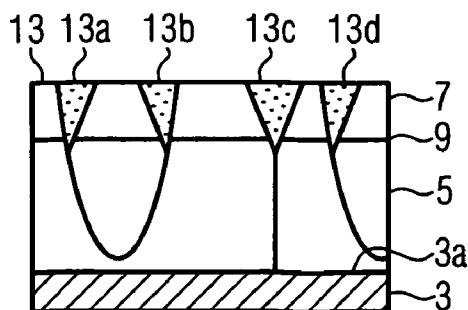


FIG. 1d

(57) Abstract: The present invention relates to a method for fabricating a substrate for a semiconductor device comprising an inter-
face region (9) between a first layer (5) and a second layer (7) having different electrical properties and an exposed surface (13),
wherein at least the second layer (7) includes defects and/or dislocations, the method comprising the steps of: a) removing material at
one or more locations of the defects and/or dislocations, thereby forming pits (13a-13d), wherein the pits intersect the interface re-
gion (9), and b) passivating the pits (3a-13d). The invention also relates to a corresponding semiconductor device structure.

